



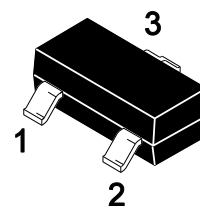
MMBD4148

Silicon Epitaxial Planar Switching Diode

Features

- High voltage
- Small package
- Small capacitance

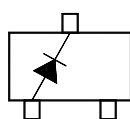
SOT-23



Equivalent Circuit

MMBD4148

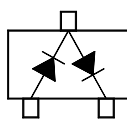
3.Cathode



1.Anode 2.NC

MMBD4148SE

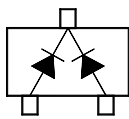
3.Cathode1、Anode2



1.Anode1 2.Cathode2

MMBD4148CC

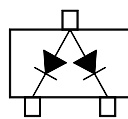
3.Cathode1、Cathode2



1.Anode1 2.Anode2

MMBD4148CA

3.Anode1、Anode2



1.Cathode1 2.Cathode2

Marking Code :

MMBD4148 : 5D

MMBD4148SE : A7

MMBD4148CC : A3

MMBD4148CA : A1

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
DC Forward Current	I_{FM}	600	mA
Repetitive Peak Forward Current	I_{FRM}	700	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	1	A
at $t = 1\text{ s}$			
at $t = 1\text{ }\mu\text{s}$		4	
Power Dissipation	P_D	350	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$



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Electrical Characteristics (T_A=25°C)

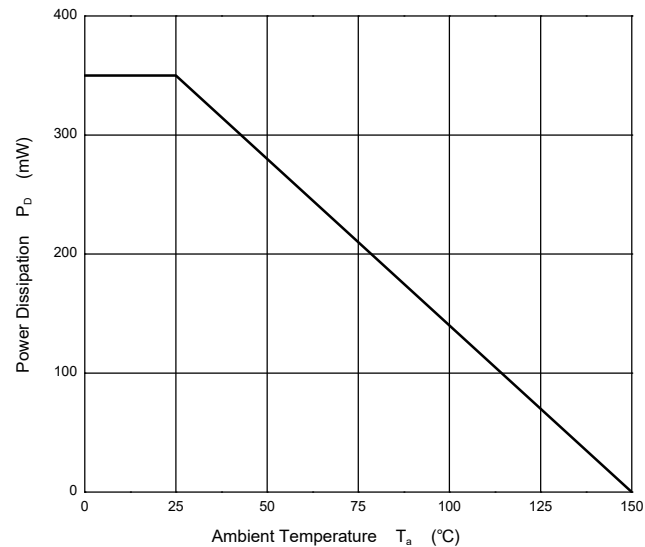
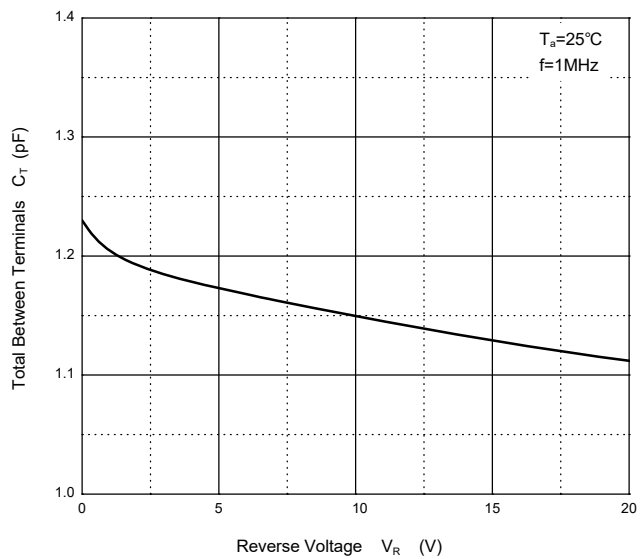
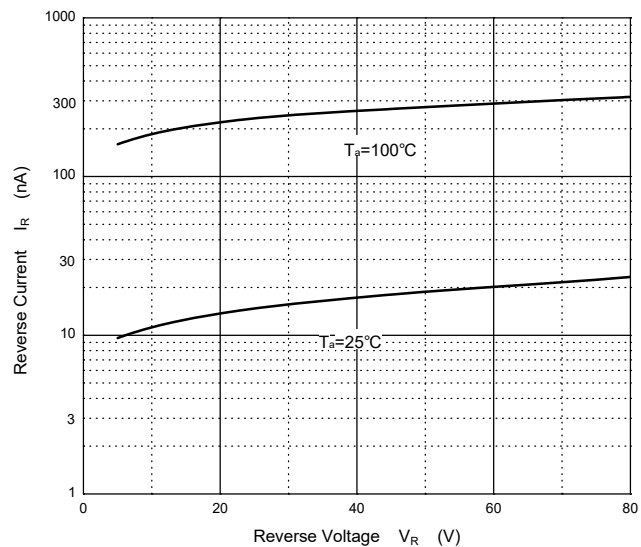
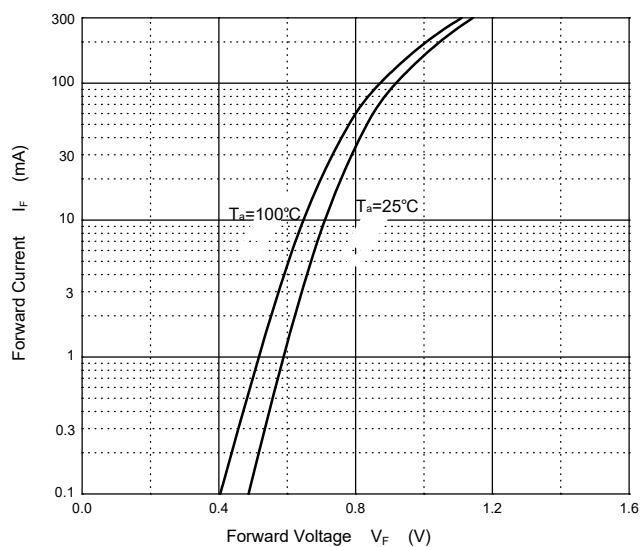
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I _F = 10 mA	V _F	--	0.85	V
Reverse Breakdown Voltage at I _R = 100 μA at I _R = 5 μA	V _{(BR)R}	100 75	-- --	V
Reverse Current at V _R = 20 V at V _R = 75 V at V _R = 20 V, at T _A = 150 °C	I _R	-- -- --	25 1 50	nA μA μA
Typical Junction Capacitance at V _R = 0 V, f = 1 MHz	C _j	--	4	pF
Maximum Reverse Recovery Time at I _F = 10 mA, V _R = 6 V, I _{RR} = 1 mA, R _L = 100 Ω	T _{rr}	--	4	nS



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Typical Characteristic Curves





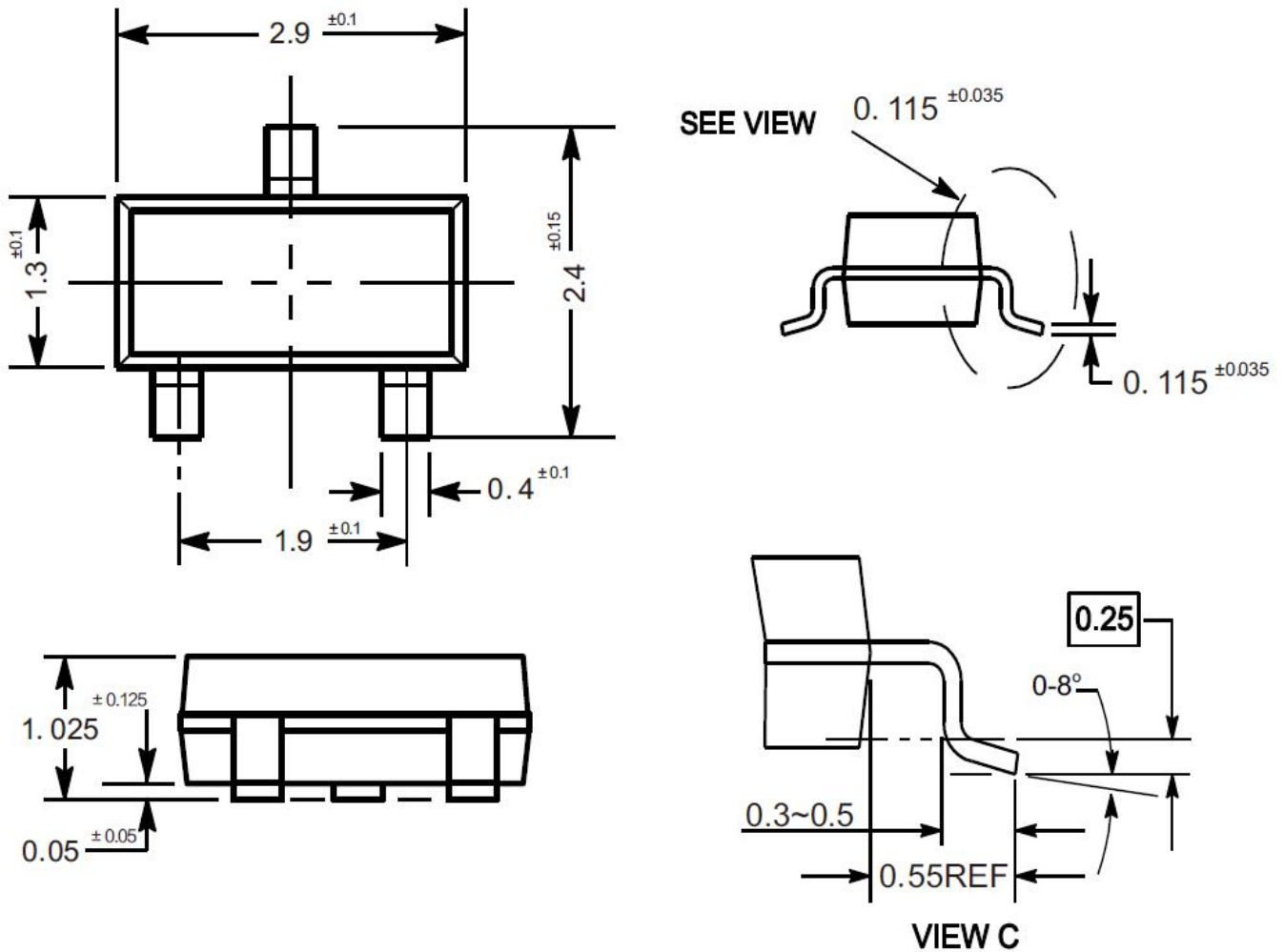
MMBD4148

Silicon Epitaxial Planar Switching Diode

Package Outline

SOT-23

Dimensions in mm



Ordering Information

Device	Package	Shipping
MMBD4148	SOT-23	3,000PCS/Reel&7inches